

BZT52C2V0S-Q1 Thru BZT52C75S-Q1**List**

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BZT52C2V0S-Q1 Thru BZT52C75S-Q1

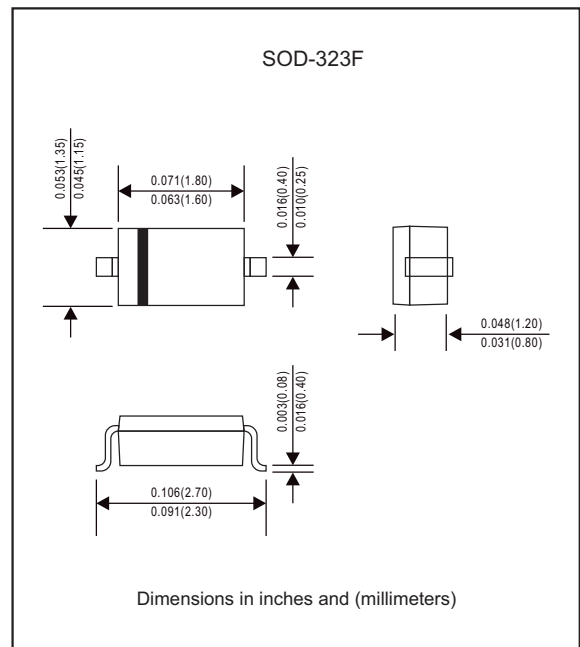
**200mW Surface Mount
Zener Diodes 2.0V-75V**

Features

- Silicon epitaxial planar chip structure
- Wide zener reverse voltage range 2.0V to 75V
- Small package size for high density applications
- Ideally suited for automated assembly processes
- Pb-free package is available
- Lead-free parts meet RoHS requirements
- Qualified to AEC-Q101 standards for high reliability
- Suffix "-H" indicates Halogen-free part, ex. BZT52C2V0S-Q1-H

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-323F
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.005 gram

Package outline**Maximum ratings** (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	Unit
Forward voltage	$I_F=10\text{mA}$	V_F			0.9	V
Power dissipation	$T_A=25^\circ\text{C}$ (Note 1)	P_D			200	mW
Thermal resistance	Junction to ambient (Note 1) Junction to case (Note 1)	$R_{\theta JA}$ $R_{\theta JC}$		625 350		$^\circ\text{C/W}$ $^\circ\text{C/W}$
Operating junction temperature range		T_J	-55		+150	$^\circ\text{C}$
Storage temperature range		T_{STG}	-55		+150	$^\circ\text{C}$

Note 1: Mounted on FR-4 minimum pad

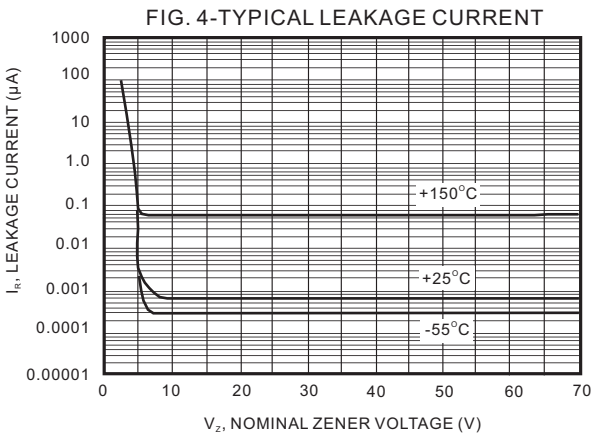
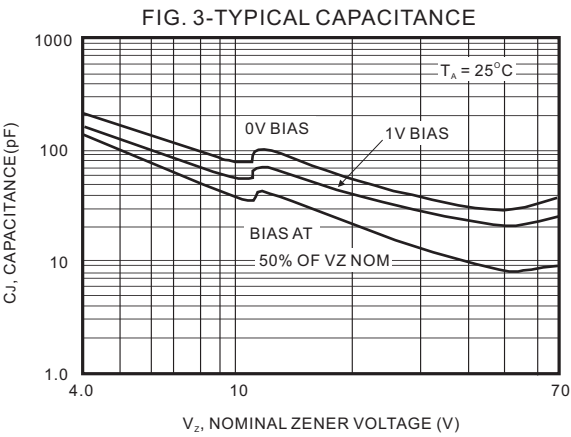
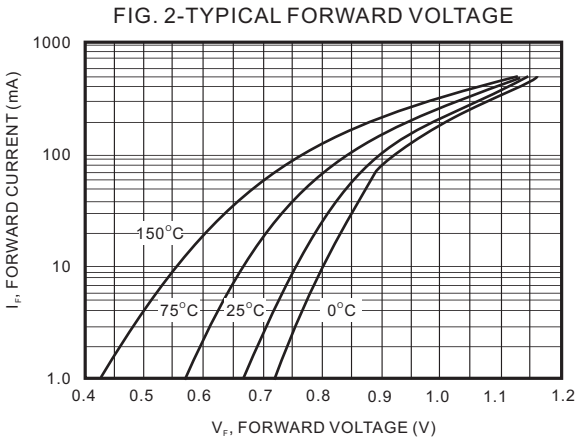
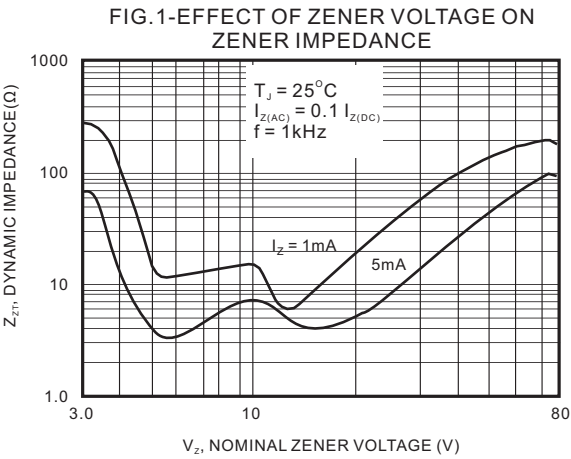
BZT52C2V0S-Q1 Thru BZT52C75S-Q1

Electrical characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Part No.	Marking code	Zener voltage			Test current	Zener Impedance			Leakage current		θV _z @I _{zt}		C _J
		V _z @ I _{ZT}			I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	I _{ZK}	I _R	V _R	mV/k	mV/k	@VR=0V f=1MHz
		Min.(V)	Nom.(V)	Max.(V)	mA	Max.(Ω)	Max.(Ω)	mA	Max.(μA)	Volts	Min.	Max.	Typ.(pF)
BZT52C2V0S-Q1	WY,ZB	1.91	2.0	2.09	5	100	600	1.0	150.0	1.0	-3.5	0	450
BZT52C2V4S-Q1	00,W0	2.2	2.4	2.6	5	100	1000	0.5	50.0	1.0	-3.5	0	450
BZT52C2V7S-Q1	01,W1	2.5	2.7	2.9	5	100	1000	0.5	20.0	1.0	-3.5	0	450
BZT52C3V0S-Q1	02,W2	2.8	3.0	3.2	5	100	1000	0.5	10.0	1.0	-3.5	0	450
BZT52C3V3S-Q1	05,W3	3.1	3.3	3.5	5	95	1000	0.5	5.0	1.0	-3.5	0	450
BZT52C3V6S-Q1	06,W4	3.4	3.6	3.8	5	90	1000	0.5	5.0	1.0	-3.5	0	450
BZT52C3V9S-Q1	07,W5	3.7	3.9	4.1	5	90	1000	0.5	3.0	1.0	-3.5	-2.5	450
BZT52C4V3S-Q1	08,W6	4.0	4.3	4.6	5	90	1000	0.5	3.0	1.0	-3.5	0	450
BZT52C4V7S-Q1	09,W7	4.4	4.7	5.0	5	80	800	0.5	3.0	2.0	-3.5	0.2	260
BZT52C5V1S-Q1	0A,W8	4.8	5.1	5.4	5	60	800	0.5	2.0	2.0	-2.7	1.2	225
BZT52C5V6S-Q1	0C,W9	5.2	5.6	6.0	5	40	700	0.5	1.0	2.0	-2.0	2.5	200
BZT52C6V2S-Q1	0E,WA	5.8	6.2	6.6	5	10	100	0.5	3.0	4.0	0.4	3.7	185
BZT52C6V8S-Q1	0F,WB	6.4	6.8	7.2	5	15	160	0.5	2.0	4.0	1.2	4.5	155
BZT52C7V5S-Q1	0G,WC	7.0	7.5	7.9	5	15	160	0.5	1.0	5.0	2.5	5.3	140
BZT52C8V2S-Q1	0H,WD	7.7	8.2	8.7	5	15	160	0.5	0.7	5.0	3.2	6.2	135
BZT52C9V1S-Q1	0K,WE	8.5	9.1	9.6	5	15	160	0.5	0.2	7.0	3.8	7.0	130
BZT52C10S-Q1	0L,WF	9.4	10	10.6	5	20	160	0.5	0.1	8.0	4.5	8.0	130
BZT52C11S-Q1	0M,WG	10.4	11	11.6	5	20	160	0.5	0.1	8.0	5.4	9.0	130
BZT52C12S-Q1	0N,WH	11.4	12	12.7	5	25	80	0.5	0.1	8.0	6.0	10	130
BZT52C13S-Q1	0P,WI	12.4	13	14.1	5	30	80	0.5	0.1	8.0	7.0	11	120
BZT52C15S-Q1	0T,WJ	14.3	15	15.8	5	30	400	0.5	0.05	10.5	9.2	13	110
BZT52C16S-Q1	0U,WK	15.3	16	17.1	5	40	400	0.5	0.05	11.2	10.4	14	105
BZT52C18S-Q1	0W,WL	16.8	18	19.1	5	45	400	0.5	0.05	12.6	12.4	16	100
BZT52C20S-Q1	0Z,WM	18.8	20	21.2	5	55	500	0.5	0.05	14.0	14.4	18	85
BZT52C22S-Q1	10,WN	20.8	22	23.3	5	55	500	0.5	0.05	15.4	16.4	20	85
BZT52C24S-Q1	11,WO	22.8	24	25.6	5	70	120	0.5	0.05	16.8	18.4	22	80
BZT52C27S-Q1	12,WP	25.1	27	28.9	2	80	300	0.5	0.05	18.9	21.4	25.3	70
BZT52C30S-Q1	14,WQ	28	30	32	2	80	300	0.5	0.05	21.0	24.4	29.4	70
BZT52C33S-Q1	18,WR	31	33	35	2	80	300	0.5	0.05	23.2	27.4	33.4	70
BZT52C36S-Q1	19,WS	34	36	38	2	90	500	0.5	0.05	25.2	30.4	37.4	70
BZT52C39S-Q1	20,WT	37	39	41	2	130	500	0.5	0.05	27.3	33.4	41.2	45
BZT52C43S-Q1	21,WU	40	43	46	2	150	500	0.5	0.05	30.1	37.6	46.6	40
BZT52C47S-Q1	1A,WV	44	47	50	2	170	500	0.5	0.05	32.9	42.0	51.8	40
BZT52C51S-Q1	1C,WW	48	51	54	2	180	500	0.5	0.05	35.7	46.6	57.2	40
BZT52C56S-Q1	1D,WX	52	56	60	2	200	500	0.5	0.05	39.2	52.2	63.8	40
BZT52C62S-Q1	1E,WY	58	62	66	2	215	500	0.5	0.05	43.4	58.8	71.6	35
BZT52C68S-Q1	1F,WZ	64	68	72	2	240	500	0.5	0.05	47.6	65.6	79.8	35
BZT52C75S-Q1	1G,ZA	70	75	79	2	255	500	0.5	0.05	52.5	73.4	88.6	35

Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C .

Rating and characteristic curves (BZT52C2V0S-Q1 Thru BZT52C75S-Q1)



Rating and characteristic curves (BZT52C2V0S-Q1 Thru BZT52C75S-Q1)

FIG. 5-ZENER VOLTAGE VERSUS ZENER CURRENT
(V_z UP TO 12V)

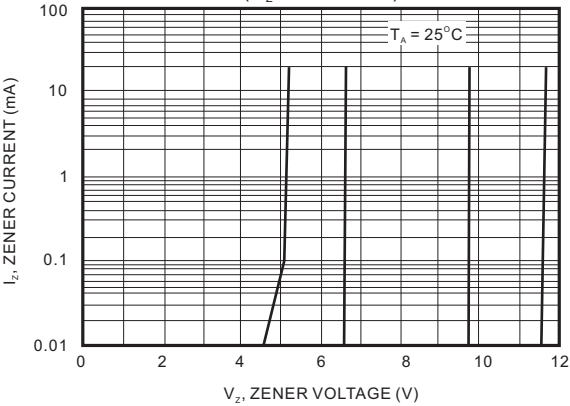


FIG. 6-ZENER VOLTAGE VERSUS
ZENER CURRENT (12V TO 75V)

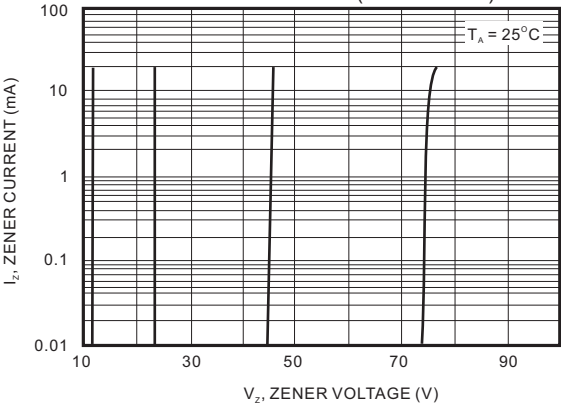
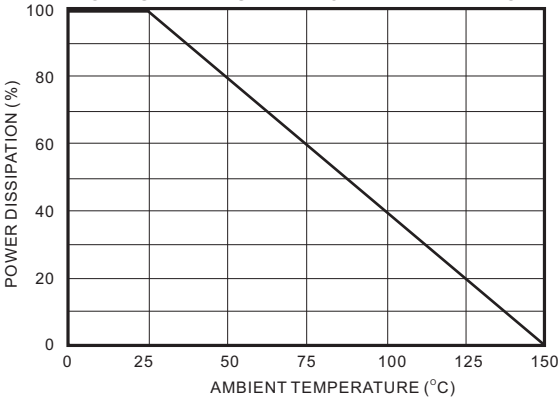
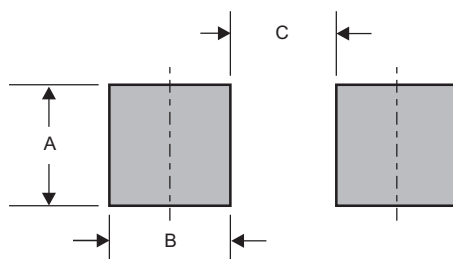


FIG. 7-STEADY STATE POWER DERATING



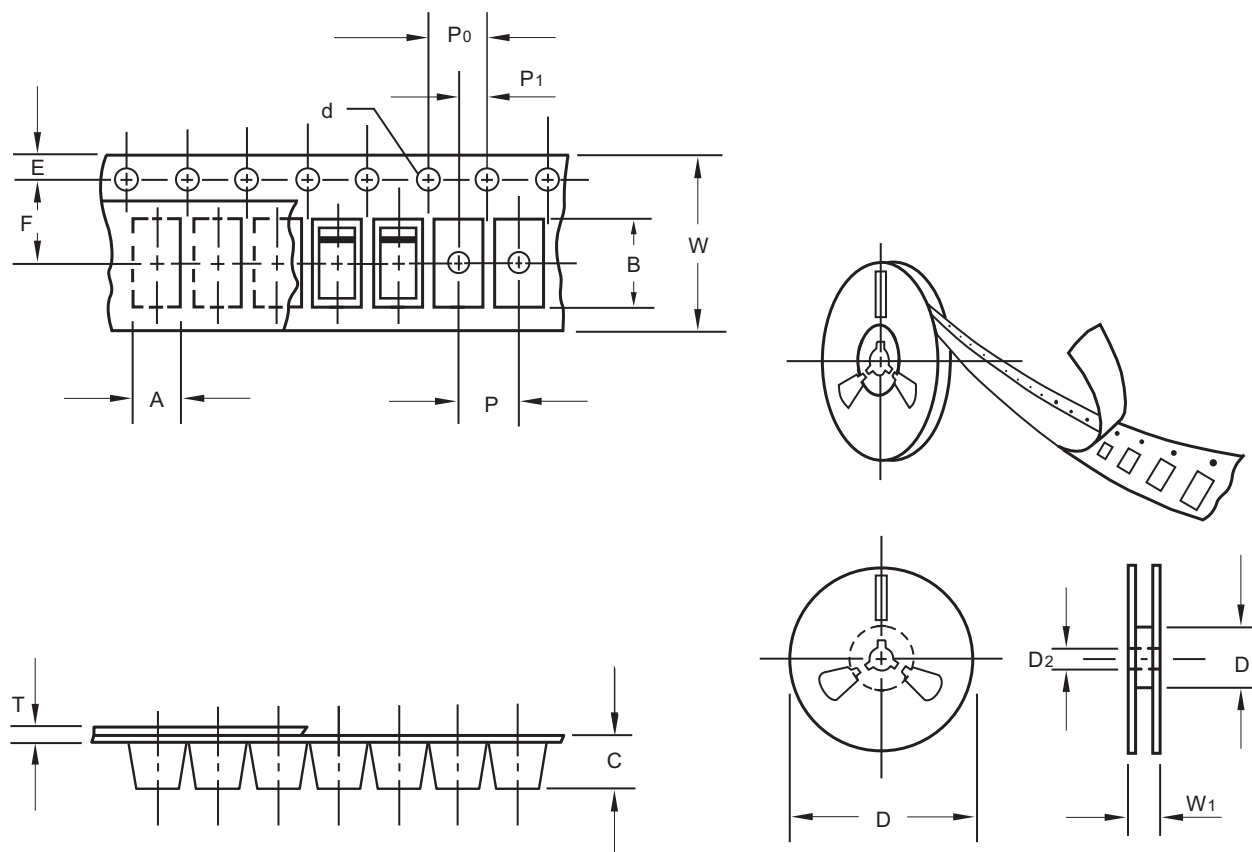
BZT52C2V0S-Q1 Thru BZT52C75S-Q1**Pinning information**

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Suggested solder pad layout

Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-323F	0.033 (0.83)	0.025 (0.63)	0.063 (1.60)

BZT52C2V0S-Q1 Thru BZT52C75S-Q1**Packing information**

unit:mm

Item	Symbol	Tolerance	SOD-323F
Carrier width	A	0.1	1.46
Carrier length	B	0.1	2.95
Carrier depth	C	0.1	1.25
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D ₁	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	62.00
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W ₁	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

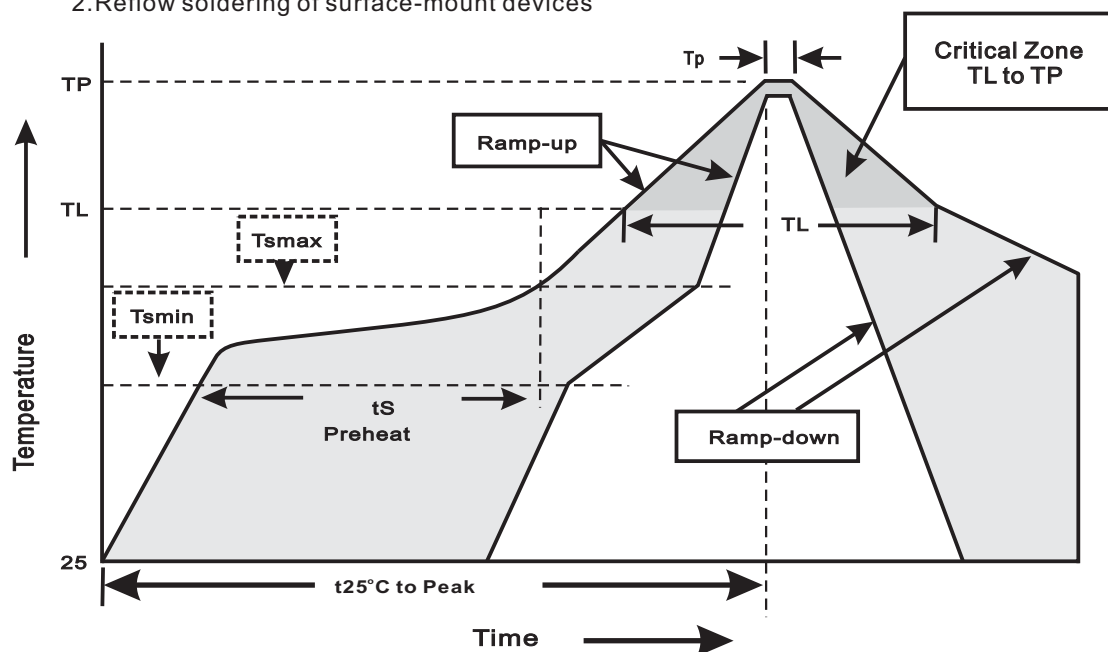
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-323F	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	8.0

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(TL to TP)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min to max)(ts)	150°C 200°C 60~120sec
Tsmax to TL -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(TL) -Time(tL)	217°C 60~260sec
Peak Temperature(Tp)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(tp)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

BZT52C2V0S-Q1 Thru BZT52C75S-Q1**High reliability test capabilities**

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%R.H. + 3xIR@260°C + 1flux immersion + alcohol + DI H ₂ O rinse	JESD22-A113
2. High Temperature Reverse Bias	V _z = V _z NOM * 80% (T _J max = 150°C) Test Duration: 1000hrs	JESD22-A108
3. High Temperature Storage Life	T _a =125°C Test Duration: 1000hrs	JESD22A-103
4. Temperature Cycling	-55°C(15min) to 150°C (15min) Test Cycles: 1000cycles	JESD22A-104
5. Autoclave	P=2atm., T _a =121°C, R.H.=100% Test Duration: 96hrs	JESD22A-102
6. Solderability	245±5°C for 5 sec.	J-STD-002
7. Moisture Resistance	T _a =85°C/85% Relative humidity Test Duration: 1000hrs	MIL-STD-750E METHOD-1021.2
8. Resistance To Solder Heat	260±5°C for 10sec.	JESD22B-106
9. High Temperature High Humidity Reverse Bias	T _a =85°C,85%R.H.,with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration: 1000hrs	JESD22-A101